

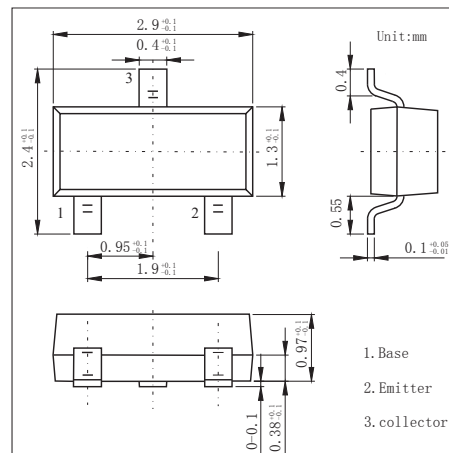
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Complementary to 2SC1623
- High DC Current Gain: $h_{FE}=200$ TYP. ($V_{CE}=-6V, I_C=-1mA$)
- High Voltage: $V_{ceo}=-50V$
- PNP TRANSISTORS
- Collector-Base Voltage: $V_{CBO}=-60V$

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$		-0.1		μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1		μA
DC current gain	h_{FE}		90		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.3	V
Base-emitter voltage	V_{BE}	$I_C=-1mA, V_{CE}=-6V$	-0.58	-0.68		V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-10mA$	180			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		4.5		pF

RATINGS AND CHARACTERISTIC CURVES

